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a plurality of projected portions over said substrate;

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface~~, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more~~; and

a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film,

wherein said projected surface of said pixel electrode has a radius of curvature from 0.1 to 4 μm.

2 (original). The semiconductor device according to claim 1, wherein said projected portions comprise a same material as one selected from the group consisting of a semiconductor layer, a gate electrode, and a gate insulating film of said thin film transistor.

3 (original). The semiconductor device according to claim 1, wherein said projected portions have different heights or different shapes.

4 (original). The semiconductor device according to claim 1, wherein said pixel electrode comprises one selected from the group consisting of Al, Ag, and a lamination of Al and Ag.

5 (original). The semiconductor device according to claim 1, further comprising a first light shielding portion comprising laminated layers of a first color layer and a second color layer; and

a second light shielding portion comprising laminated layers of said first color layer and a third color layer;

wherein said first light shielding portion and said second light shielding portion are formed to overlap in an interval between an arbitrary one of said pixel electrode and said pixel electrode contiguous to said arbitrary one of said pixel electrode.

6 (original). The semiconductor device according to claim 5, wherein said first color layer comprises a red color, said second color layer comprises a blue color, and said third color layer comprises a green color.

7 (original). The semiconductor device according to claim 5, wherein said first light shielding portion and said second light shielding portion are provided over an opposed substrate.

8 (original). The semiconductor according to claim 1, wherein said semiconductor device is a reflection type liquid crystal display device.

9 (previously amended). The semiconductor device according to claim 1, wherein said semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a portable telephone, a goggle-type display, a digital camera, a player using a recording medium, and a portable electronic book.

10 (currently amended). A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;

a plurality of projected portions on said insulating surface;

~~an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more;~~ and

a pixel electrode having a projected and recessed surface ~~on said interlayer insulating film~~, and electrically connected to said thin film transistor,

wherein said projected surface of said pixel electrode has a radius of curvature from 0.1 to 4 μm.

11 (original). The semiconductor device according to claim 10, wherein said projected portions comprise a same material as one selected from the group consisting of a semiconductor layer, a gate electrode, and a gate insulating film of said thin film transistor.

12 (original). The semiconductor device according to claim 10, wherein said projected portions have different heights or different shapes.

13 (original). The semiconductor device according to claim 10, wherein said pixel electrode comprises one selected from the group consisting of Al, Ag, and a lamination of Al and Ag.

14 (original). The semiconductor device according to claim 10, further comprising a first light shielding portion comprising laminated layers of a first color layer and a second color layer; and

a second light shielding portion comprising laminated layers of said first color layer and a third color layer;

wherein said first light shielding portion and said second light shielding portion are formed to overlap in an interval between an arbitrary one of said pixel electrode and said pixel electrode contiguous to said arbitrary one of said pixel electrode.

15 (original). The semiconductor device according to claim 14, wherein said first color layer comprises a red color, said second color layer comprises a blue color, and said third color layer comprises a green color.

16 (original). The semiconductor device according to claim 14, wherein said first light shielding portion and said second light shielding portion are provided over an opposed substrate.

17 (original). The semiconductor according to claim 10, wherein said semiconductor device is a reflection type liquid crystal display device.

18 (previously amended). The semiconductor device according to claim 10, wherein said semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a portable telephone, a goggle-type display, a digital camera, a player using a recording medium, and a portable electronic book.

19 (currently amended). A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer over a substrate and a gate electrode with an insulating film interposed therebetween;

a plurality of projected portions over said substrate;

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface~~, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more~~; and

a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film,

wherein said projected surface of said pixel electrode has a radius of curvature from 0.1 to 4 μm.

20 (original). The semiconductor device according to claim 19, wherein said projected portions have different heights or different shapes.

21 (original). The semiconductor device according to claim 19, wherein said pixel electrode comprises one selected from the group consisting of Al, Ag, and a lamination of Al and Ag.

22 (original). The semiconductor device according to claim 19, further comprising a first light shielding portion comprising laminated layers of a first color layer and a second color layer; and

a second light shielding portion comprising laminated layers of said first color layer and a third color layer;

wherein said first light shielding portion and said second light shielding portion are formed to overlap in an interval between an arbitrary one of said pixel electrode and said pixel electrode contiguous to said arbitrary one of said pixel electrode.

23 (original). The semiconductor device according to claim 22, wherein said first color layer comprises a red color, said second color layer comprises a blue color, and said third color layer comprises a green color.

24 (original). The semiconductor device according to claim 22, wherein said first light shielding portion and said second light shielding portion are provided over an opposed substrate.

25 (original). The semiconductor according to claim 19, wherein said semiconductor device is a reflection type liquid crystal display device.

26 (previously amended). The semiconductor device according to claim 19, wherein said semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a portable telephone, a goggle-

type display, a digital camera, a player using a recording medium, and a portable electronic book.

27 (currently amended). A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;

a plurality of projected portions on said insulating film;

~~an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more;~~ and

a pixel electrode having a projected and recessed surface ~~on said interlayer insulating film~~, and electrically connected to said thin film transistor,

wherein said projected surface of said pixel electrode has a radius of curvature from 0.1 to 4 μm.

28 (previously amended). The semiconductor device according to claim 27, wherein said projected portions comprise a same material as a gate electrode of said thin film transistor.

29 (original). The semiconductor device according to claim 27, wherein said projected portions have different heights or different shapes.

30 (original). The semiconductor device according to claim 27, wherein said pixel electrode comprises one selected from the group consisting of Al, Ag, and a lamination of Al and Ag.

31 (original). The semiconductor device according to claim 27, further comprising a first light shielding portion comprising laminated layers of a first color layer and a second color layer; and

a second light shielding portion comprising laminated layers of said first color layer and a third color layer;

wherein said first light shielding portion and said second light shielding portion are formed to overlap in an interval between an arbitrary one of said pixel electrode and said pixel electrode contiguous to said arbitrary one of said pixel electrode.

32 (original). The semiconductor device according to claim 31, wherein said first color layer comprises a red color, said second color layer comprises a blue color, and said third color layer comprises a green color.

33 (original). The semiconductor device according to claim 31, wherein said first light shielding portion and said second light shielding portion are provided over an opposed substrate.

34 (original). The semiconductor according to claim 27, wherein said semiconductor device is a reflection type liquid crystal display device.

35 (previously amended). The semiconductor device according to claim 27, wherein said semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a portable telephone, a goggle-type display, a digital camera, a player using a recording medium, and a portable electronic book.

36-53 (previously canceled).